

ABSTRACT

This method of cleaning a SiC monocrystal growth furnace uses a gas to clean a SiC monocrystal growth furnace provided with an in-furnace substrate composed of a 3C-SiC polycrystal having at least a surface in which an intensity ratio of a (111) plane with respect to other crystal planes is at least 85% but not more than 100% according to powder XRD analysis, the method including flowing a mixed gas of fluorine gas and at least one of an inert gas and air in a non-plasma state through the inside of the SiC monocrystal growth furnace, thereby selectively removing a SiC deposit deposited inside the SiC monocrystal growth furnace, wherein the mixed gas comprises at least 1 vol% but not more than 20 vol% of fluorine gas, and at least 80 vol% but not more than 99 vol% of an inert gas, and a temperature inside the SiC monocrystal growth furnace is at least 200°C but not more than 500°C.